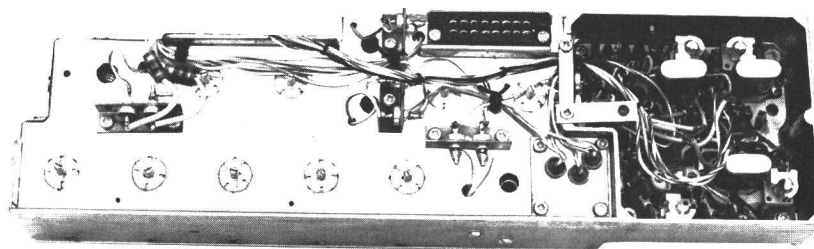


# MASTR<sup>®</sup> PROGRESS LINE

450-470 MHz DUAL FRONT END MODELS 19D413487-G1 & G2



## SPECIFICATIONS \*

DUAL FRONT END 19D413487G1: With Pre-Amp  
 DUAL FRONT END 19D413487G2: Without Pre-Amp

FREQUENCY RANGE	450-470 MHz	
SENSITIVITY (DFE & RECEIVER)	With Pre-Amp	Without Pre-Amp
12 dB SINAD	0.35 $\mu$ V	0.60 $\mu$ V
20 dB Quieting	0.40 $\mu$ V	0.70 $\mu$ V
INTERMODULATION (EIA)	-70 dB	
INPUT POWER	.010 Amps at 10 volts	
FREQUENCY STABILITY		
Standard Oscillator	$\pm$ .0005% (-30°C to +60°C)	
ICOM Oscillator	$\pm$ .0002% (-30°C to +60°C)	
DIMENSIONS (HxWxD)	2-14" x 11-3/4" x 4-3/8"	

## OPTIONS

7351:	1-Freq. Standard	7356:	3-Freq. with Pre-Amp
7352:	2-Freq. Standard	7357:	1-Freq. with ICOM Osc.
7353:	3-Freq. Standard	7358:	2-Freq. with ICOM Osc.
7354:	1-Freq. with Pre-Amp	7359:	3-Freq. with ICOM Osc.
7355:	2-Freq. with Pre-Amp		

\*These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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## DESCRIPTION

### DUAL FRONT END

General Electric Dual Front End Models 19D413487-G1 & G2 were designed for operation in the 450—470 megahertz band. The Dual Front End (DFE) is used with MASTR Progress Line Receivers to monitor up to four frequencies when the channel spacing is greater than 0.4% ( $\pm 0.2\%$ ).

The DFE is of single-unit construction, completely housed in an aluminum casting for maximum shielding and rigidity. The standard unit consists of five helical resonators, 1st mixer, oscillator and three

multiplier stages, and a high IF amplifier.

An optional RF amplifier stage is available whenever an increase in sensitivity is required. The chassis is mounted in a housing on the rear of the mobile frame, adding approximately three inches to the overall length of the mobile unit. A block diagram of the DFE is shown in Figure 1.

### ANTENNA SYSTEM

The Dual Front End and the receiver use a common antenna. A power splitter mounted on the front of the system frame provides approximately 20 dB separation for the two to four receive channels. Due to

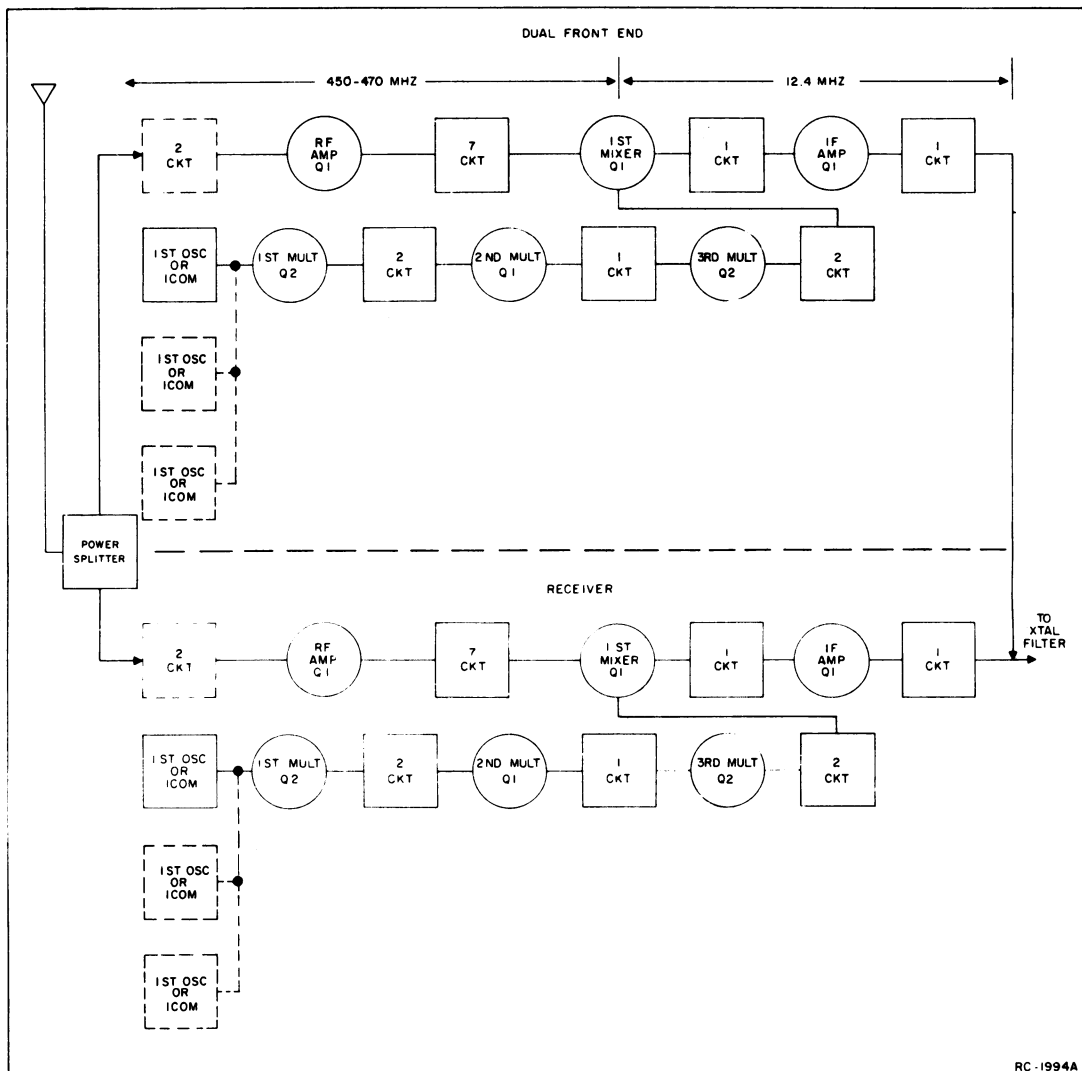


Figure 1 - Dual Front End Block Diagram

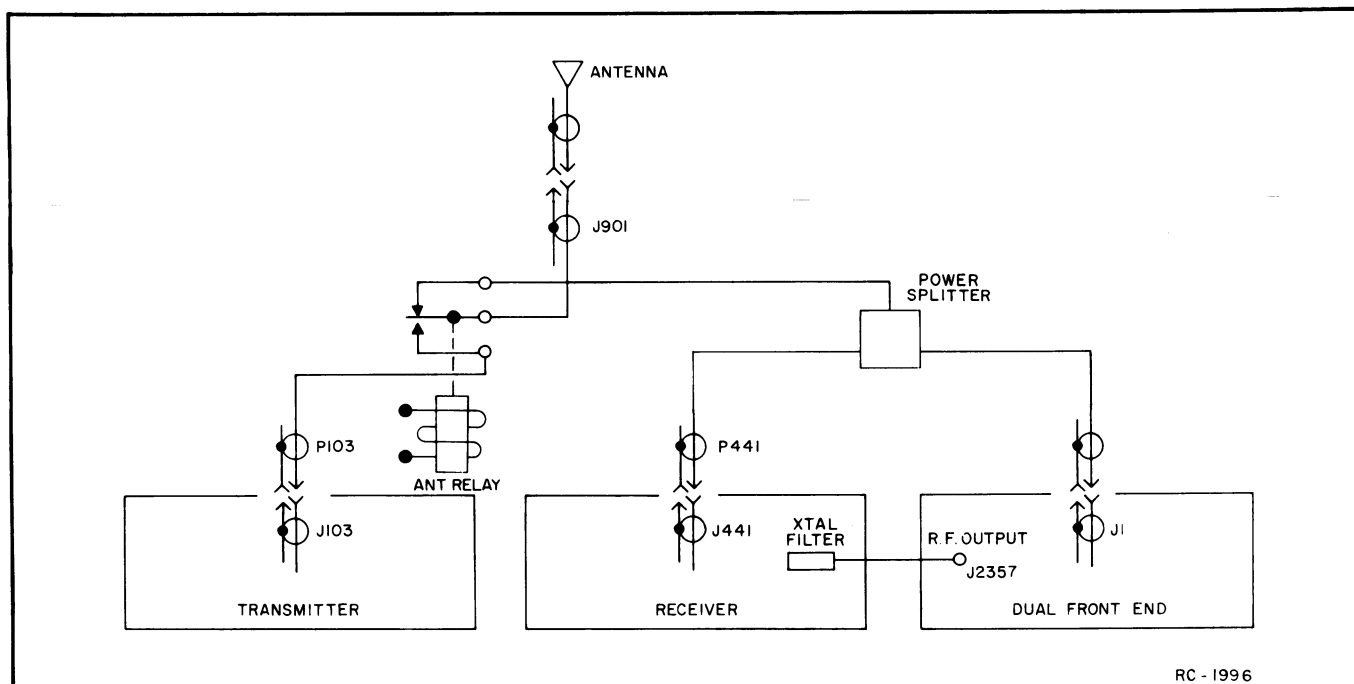


Figure 2 - Single Antenna Block Diagram

the isolation provided by the power splitter, cable lengths to the DFE and the receiver are not critical.

In standard applications, the antenna connects to J901 on the front of the mobile unit. From J901, the antenna connects to the common terminal of the antenna relay (See Figure 2). The transmitter connects to the normally-open contact on the antenna relay, while the normally-closed contact is connected to input jack J3 on the power splitter.

One cable from the power splitter connects to the DFE input jack J1, and the other cable connects to J441 on the receiver.

## CIRCUIT ANALYSIS

The MASTR Progress Line Dual Front End is completely transistorized, using six silicon transistors. A regulated 10 volts is used for all stages of the Dual Front End.

Centralized metering jack J2352 is provided for use with GE Test Set Models 4EX3A10 and 4EX8K11 for ease of alignment and servicing. The Test Set meters the oscillator, multipliers, and the regulated 10 volts.

The regulated 10 volts, oscillator keying voltages system negative, and ground connections are supplied by the two cables from receiver plug P443.

## RF AMPLIFIER A2352

RF Amplifier A2352 is used only in ultra-high sensitivity (UHS) Dual Front Ends and consists of two tuned helical resonators and an RF amplifier (Q1).

RF from the antenna is coupled through W2354 to a tap on L2353. The tap is positioned to provide the proper impedance match to the antenna. RF energy is coupled to L2354 through an opening in the shield wall, and then to the Base of Q1. The amplified output is taken from the collector of Q1 and coupled through C2 and W2353 to the input of fine helical resonators.

## HELICAL RESONATORS

In DFE's without the UHS option, the RF selectivity is provided by five tuned helical resonators L2360 through L2365. RF cable W2355 connects the RF signal from the antenna to a tap on L2360. The tap is positioned to provide the proper impedance match to the antenna. The output of L2365 is coupled through capacitor C1 to the 1st mixer assembly.

## STANDARD OSCILLATOR/MULTIPLIER (A2359)

The standard 1st oscillator operates in a transistorized Colpitts oscillator circuit. The oscillator crystal operates in a fundamental mode at a frequency of approximately 16 to 19 megahertz. The crystal is cut to provide temperature compensation at the high end of the temperature range and is thermistor compensated at low temperatures. This provides  $\pm 0.0005\%$  frequency stability as soon as the power is applied -- without having to wait for crystal ovens to warm up.

A four-frequency 1st oscillator/multiplier board is provided with the DFE. The proper frequency is selected by switching the desired crystal circuit to +10 volts by means of a frequency selector switch on the control unit. See Figure 3 for the available frequency combinations.

Receiver	D.F.E.
1 Freq.	1 Freq.
1 Freq.	2 Freq.
1 Freq.	3 Freq.
2 Freq.	1 Freq.
2 Freq.	2 Freq.
3 Freq.	1 Freq.

Figure 3 - Frequency Combinations

Regulated 10 volts is supplied to the crystal circuit to forward bias one of the four diodes CR1-CR4. Forward biasing the diode reduces its impedance, so that the crystal frequency is applied to the base of oscillator is developed across C47. The oscillator output is coupled through C45 to the base of 1st multiplier Q2.

The 1st multiplier output is coupled through T8 to Multiplier Board A2355. T8 is tuned to four times the crystal frequency. The 1st multiplier stage is metered at J2352-4 through metering network C38, CR6, R17 and R18.

## OSCILLATOR MULTIPLIER WITH ICOM (A2375)

Oscillator/Multiplier Board A2375 uses ICOM Module Model 4EG26A10. The ICOM Module consists of a crystal-controlled Colpitts oscillator, a voltage regulated and a buffer output stage. The entire module (including crystal) is enclosed in a dust-proof

aluminum can, with the ICOM frequency and the receiver printed on the top. Access to the oscillator trimmer is obtained by prying off the plastic GE decal on the top of the can.

The oscillator frequency is temperature-compensated at both ends of the temperature range to provide instant frequency compensation, with a frequency stability of  $\pm 0.0002\%$  without crystal ovens or warmers.

A four-frequency 1st oscillator/multiplier board is provided with the DFE. The proper frequency is selected by switching the desired ICOM circuit to +10 volts by means of a frequency selector switch on the control unit. See Figure 3 for the available frequency combinations.

In the DFE, +10 volts for operating the ICOM is obtained through the frequency selector switch on the control unit. With the ICOM operating, one of the four diodes CR1-CR4 is forward biased and the oscillator output is applied to 1st multiplier Q1.

The 1st multiplier output is coupled through T1 to multiplier board A2355. T2 is tuned to four times the ICOM frequency. The 1st multiplier stage is metered at J2352-4 through metering network C4, CR5, R5 and R6.

## CAUTION

All ICOM modules are individually compensated at the factory, and cannot be repaired in the field. Any attempt to remove the ICOM cover will void the warranty.

## MULTIPLIER BOARD (A2355)

Following the oscillator board are two multiplier stages. A2355-Q1 operates as a tripler, and Q2 operates as a doubler. Q2 is metered at J2351-1 across metering resistor R6.

The output of Q2 is coupled through two helical resonator circuits to the source terminal of the 1st mixer. The helical resonators are tuned to six times the 1st multiplier output for a total multiplication of 24 times the crystal frequency.

## 1ST MIXER (A2353)

The 1st Mixer uses a Field-Effect Transistor (FET) as the active device. A FET may be considered a semiconductor current path (or channel) whose resistance is varied by a voltage applied between the "gate" and "source" terminals. Lead identification for the FET is shown in Figure 4. The FET has voltage-controlled characteristics, and may be compared to a vacuum tube in operation (see Figure 4).

The FET mixer has several advantages over a conventional transistor mixer,

including a high input impedance and an output that is relatively free of harmonics (low in intermodulation products).

RF from the helical resonators is applied to the gate of Q1, and injection voltage from the multiplier is applied to the source. The mixer output is taken from the drain with the output tuned to the 12.4 MHz high IF frequency.

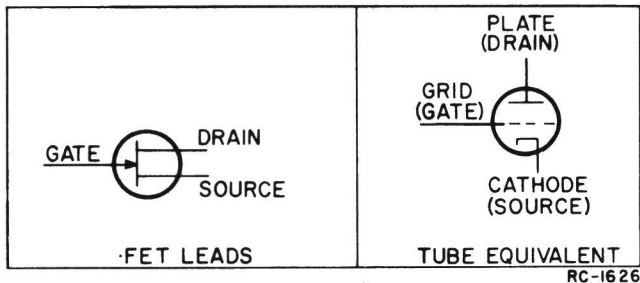


Figure 4 - FET Nomenclature

#### HI IF AMPLIFIER (A2362)

A series-resonant circuit (A2353-L2 and -C3) couples the mixer output to the emitter of the high IF amplifier A2362. The transistor is connected as a grounded-base amplifier which provides a low impedance for the mixer output. The amplifier output is coupled through transformer T1 to the crystal filter.

#### Diode Assembly 19B219305G1

The Diode Assembly 19B219305G2 is used only with 150.8-174 MHz and 450-470 MHz

Receivers and Dual Front Ends. The purpose of the diode assembly is to turn off the HI IF Amplifier and 1st Mixer of the receiver or DFE when the other is operating. Refer to Figure 5 for a typical Diode Assembly connection. Because of the many frequency combinations as shown in Figure 3, the diode assembly consists of three diodes. All unused diodes are removed.

### RECEIVER MODIFICATIONS

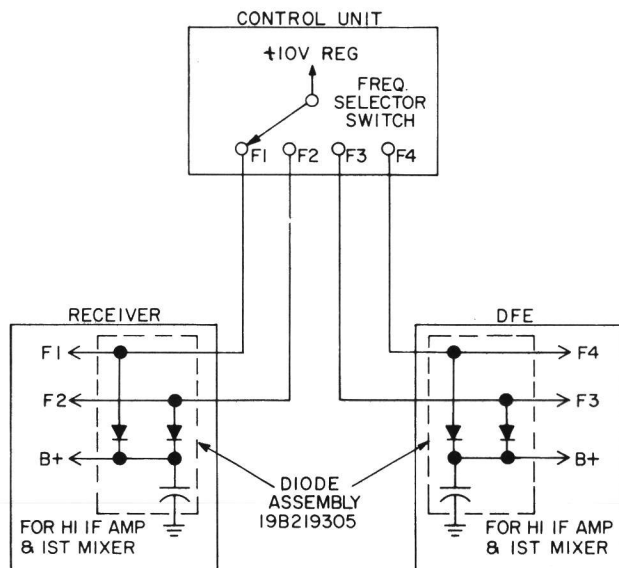
#### (MODIFICATION KIT 19A127733G1)

The MASTR mobile receiver when used with a Dual Front End option has been modified in the following manner.

1. Replaced the 3.3K-ohms resistor across the input of Crystal Filter A422 with a 10K-ohm resistor (GE Part No. 3R77-Pl03K).
2. Connected the center conductor of DFE output cable 19A127259G1 to the filter input, and the shield to the ground lug on the filter.
3. Soldered the leads from cables 19B204924G1 and 19B219302G1 to P443 as shown on the Outline Diagram (see Table of Contents).
4. Connected RF cable from the Power Splitter to J441.
5. Connected diode assembly to 1st Osc/Mult. (see Table of Contents).

### MAINTENANCE

#### DISASSEMBLY



(RC-2140)

Figure 5 - Typical Diode Assembly Connections

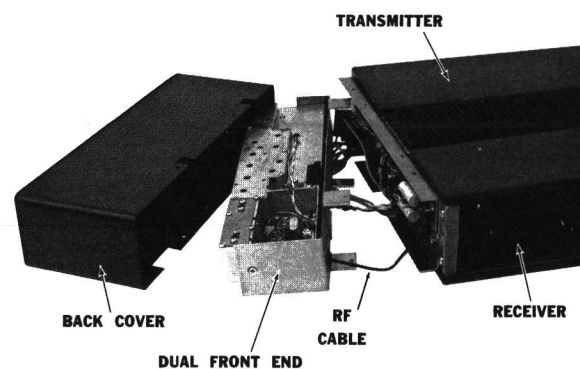


Figure 6 - Dual Front End Assembly

To gain access to the DFE:

1. Pull locking handle down and pull radio out of mounting frame.
2. Remove the four screws holding back cover to system frame. Slide cover back and lift off (see Figure 6).
3. Remove four screws from angle brackets holding Dual Front End to the system frame.
4. Carefully swing Dual Front End chassis out for servicing.

#### TEST PROCEDURES

##### Dual Front End

SYMPTOM	CHECK
No Output	<ol style="list-style-type: none"> <li>1. Connections to P443.</li> <li>2. Cable from J2357 to receiver crystal filter.</li> <li>3. Antenna terminal connections.</li> <li>4. Check 10-Volt supply with GE test meter at Pin 13 on DFE centralized metering jack J2352.</li> </ol>
Low Sensitivity	<ol style="list-style-type: none"> <li>1. DFE alignment.</li> <li>2. Cable and relay connections.</li> <li>3. 1st Mixer voltages.</li> <li>4. 1st Oscillator voltages.</li> <li>5. HI IF Amplifier voltages.</li> </ol>
Low Oscillator Reading	<ol style="list-style-type: none"> <li>1. Oscillator alignment.</li> <li>2. Voltage readings at 1st Oscillator.</li> <li>3. Crystals Y1, Y2, Y3.</li> </ol>

#### INSTRUCTIONS FOR CHANGING FREQUENCIES WHEN THE DIODE ASSEMBLY IS USED

##### GENERAL

1. To increase the number of frequencies on the Receiver or the Dual Front End. A new Diode Assembly will have to be ordered for each one or both as the case may be.
2. The diodes will be connected only to the jacks that have crystals in the respective crystal sockets.
3. There will be no more than one crystal per frequency in the receiver and Dual Front End combined.

##### PROCEDURE

1. Select the desired frequency combination and get the connection table from the following chart:

No. of Receiver Freq.	No. of DFE Freq.	Table
1	1	A
1	2	B
1	3	C
2	1	D
2	2	E
3	1	F

2. Unplug all the oscillator keying leads on the receiver and dual front end.
3. Refer to the table found in Step 1. Connect the loose end(s) of the diode(s) as follows: For the receiver, find the row that has the connections for the frequency or frequencies desired. Follow the same row across for the proper Dual Front End connection(s).
4. Clip off all unused diodes.
5. Replace the oscillator keying leads removed in step 2. Connect as shown below:

White - Yellow - Brown	to J5
White - Yellow - Red	to J4
White - Yellow - Orange	to J3
White - Yellow - Green	to J6

TABLE A

ROW	1-Freq. Receiver				1-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5					J4		
2		J4			J5			

TABLE B

ROW	1-Freq. Receiver				2-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5					J4	J3	
2			J3		J5	J4		

TABLE C

ROW	1-Freq. Receiver				3-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5					J4	J3	J6
2				J6	J5	J4	J3	

TABLE D

ROW	2-Freq. Receiver				1-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5	J4					J3	
2		J4	J3		J5			
3	J5		J3			J4		

TABLE E

ROW	2-Freq. Receiver				2-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5	J4					J3	J6
2		J4	J3		J5			J6
3			J3	J6	J5	J4		
4	J5			J6		J4	J3	
5	J5		J3			J4		J6

TABLE F

ROW	3-Freq. Receiver				1-Freq. DUAL FRONT END			
	F1	F2	F3	F4	F1	F2	F3	F4
1	J5	J4	J3					J6
2		J4	J3	J6	J5			
3	J5		J3	J6		J4		
4	J5	J4		J6			J3	

ICOM FREQUENCY ADJUSTMENT

Due to the high stability of the ICOM module, it is not recommended that zero discriminator be used as the indication for setting the oscillator frequency. Instead, measure the ICOM frequency as described in the following procedure.

EQUIPMENT REQUIRED:

- 1. Frequency Counter capable of measuring the 70-80 MHz frequency range. (The counter should have an accuracy of 0.4 part-per-million.)
- 2. Coaxial cable with test loop as described in Figure 7.
- 3. Mercury thermometer.

PROCEDURE:

- 1. Check the ICOM temperature by taping the mercury thermometer to the side of the ICOM.
- 2. Connect the frequency counter to L5 (on the 1st Osc/Mult) using the 4-turn test loop and cable shown in Figure 7.
- 3. If the ICOM temperature is 80°F (±4°F) or 26.5°C (±2°C), the frequency indication on the counter should be 4 times the frequency stenciled on the ICOM case. Adjust the ICOM trimmer (if necessary) to obtain this frequency.
- 4. If the temperature is not within the 80°F (±4°F) or 26.5°C (±2°C) range, use the correction curves of Figure 8 for setting the ICOM frequency as follows:
  - a. Check the color dot beneath the GE emblem and select the matching curve to determine the correction factor in parts-per-million (PPM).
  - b. Multiply the frequency stenciled on the ICOM by 4 and then multiply this figure by the correction factor (from Figure 8) observing the sign (±) given to the correction factor.
  - c. The frequency measured at L5 should be 4 times the ICOM frequency ± the correction factor. Adjust the ICOM trimmer (if required) to obtain this frequency.

FOR EXAMPLE

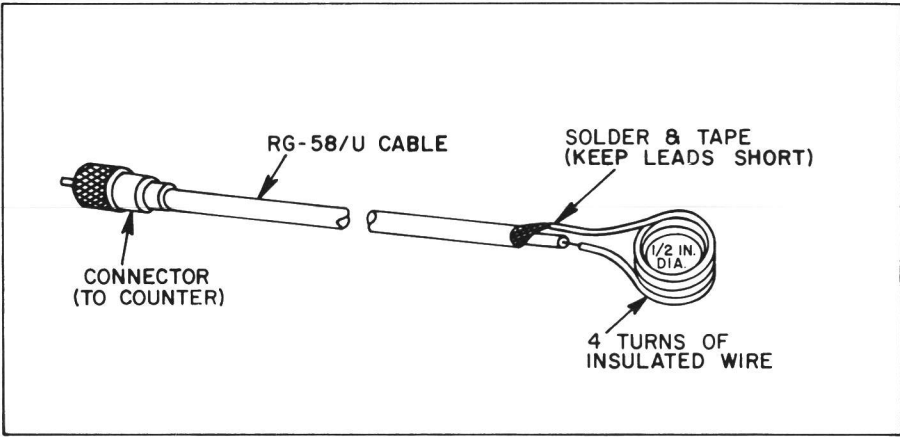
ICOM Frequency - 18.233333 MHz  
ICOM Color Dot - Green  
Ambient Temperature - 35°C (95°F)  
Correction Factor - 1.15 PPM  
(From Figure 8)

Multiply ICOM Frequency by 4;  
(18.233333 MHz x 4 = 72.933332 MHz)

Multiply preceding figure by correction factor;  
(72.933 MHz x -1.15 PPM = 83.87 hertz  
(or -84 hertz)

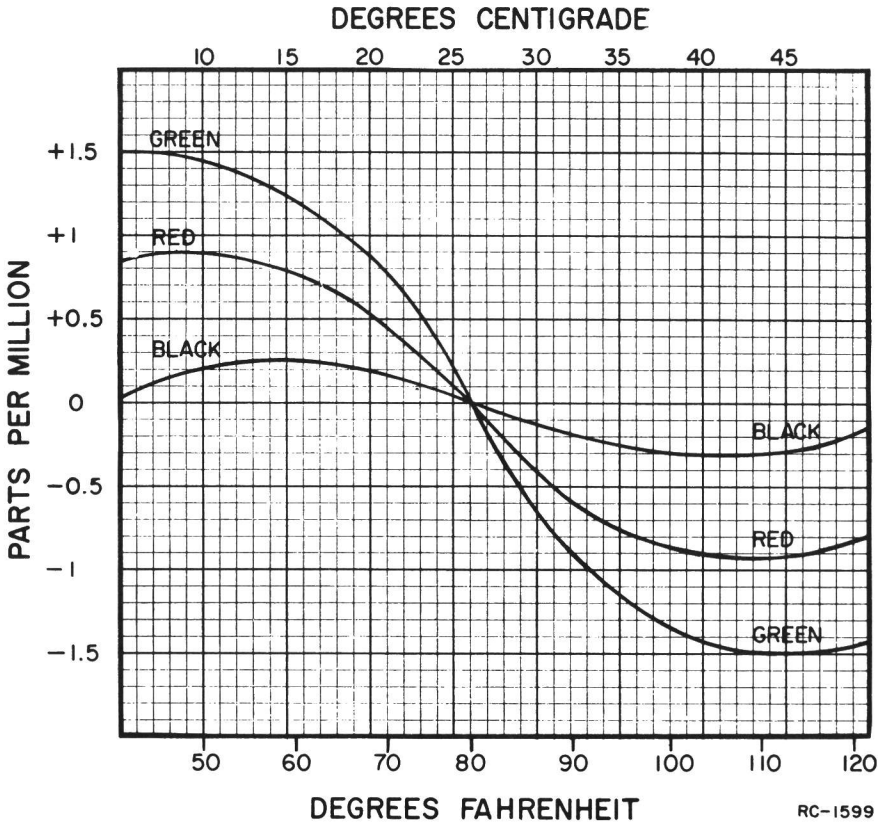
Set the frequency measured at L5 for  
72.933248 MHz;

72.933332 MHz  
- .000084 MHz  
72.933248 MHz



RC-1779

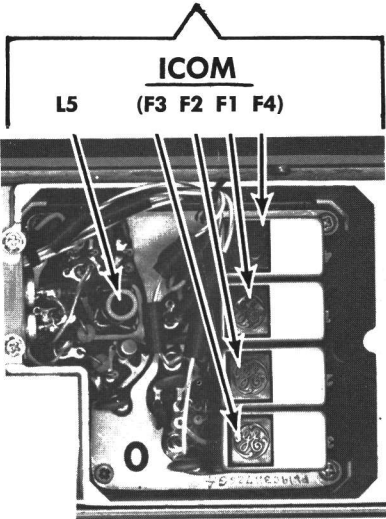
Figure 7 - Coaxial Cable and Test Loop



RC-1599

Figure 8 - ICOM Correction Curves

1st OSC/MULT. with ICOM



ADJUSTMENT PROCEDURE

ICOM ADJUSTMENT  
OSCILLATOR BOARD 19C311726G4

DUAL FRONT END ALIGNMENT

Refer to Receiver MAINTENANCE MANUAL for Receiver IF Alignment Procedure.

EQUIPMENT REQUIRED

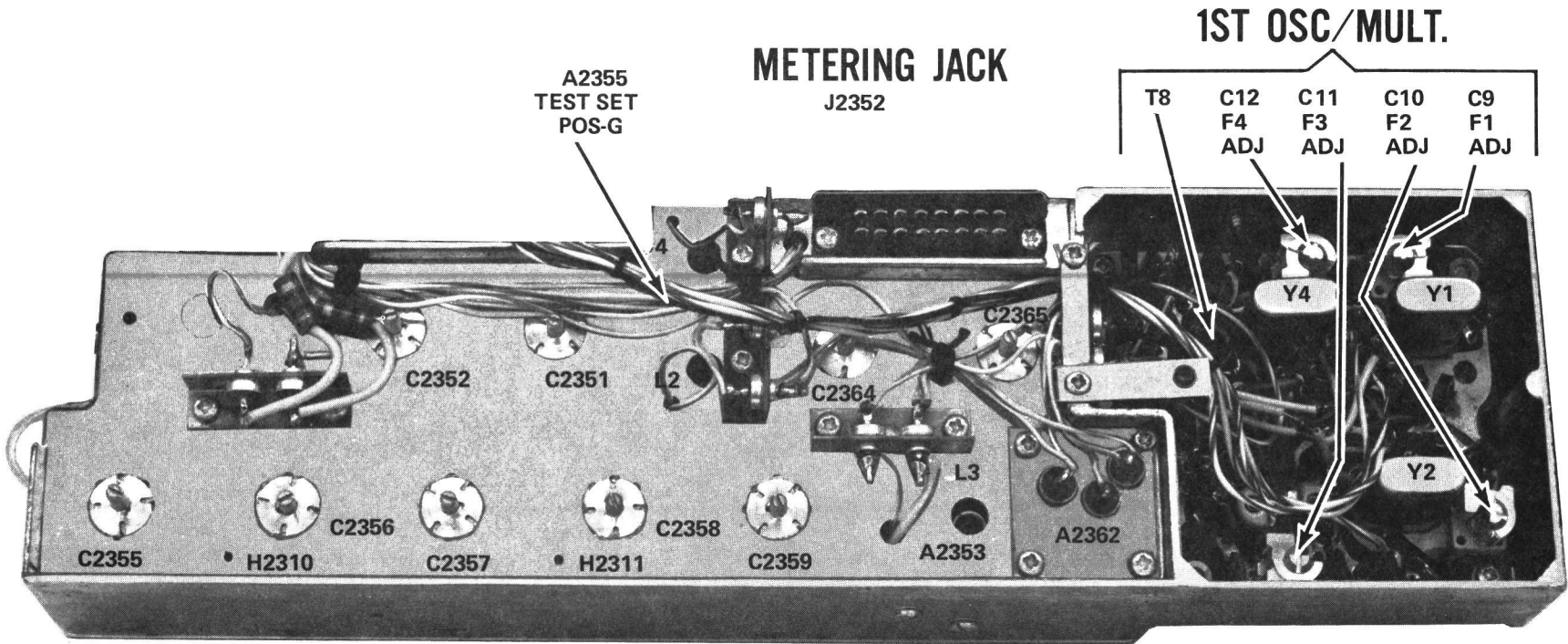
- 1. GE Test Set Models 4EX3A10 or 4EX8K11 (or a 20,000 ohm-per-volt multi-meter).
- 2. Signal Generator (450-470 MHz range). Connect a one-inch piece of insulated wire no larger than .065-inch diameter to generator output probe.

PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. Plug Test Set cable into metering jack J2352. With Test Set in position J, check for regulated +10 Volts. If using multimeter, measure at metering jack J2352-13 and -16.
- 2. If using Multimeter for alignment, connect positive lead to J2352-16 (ground).
- 3. Set the frequency selector switch on the control unit to select the center frequency of the multi-frequency DFE.
- 4. For a large change in frequency or a badly mis-aligned DFE, set crystal trimmers C9, C10, C11 and C12 on standard 1st Osc/Set board to mid-capacity. Do not touch ICOM trimmer if using ICOM oscillator.

NOTE

If Receiver and Dual Front End operating frequencies are less than 1 MHz apart, connect the signal generator directly into the Dual Front End antenna connector, not into the connector.



ALIGNMENT PROCEDURE

LBI-4245

STEP	METERING POSITION		TUNING CONTROL	METER READING	PROCEDURE
	GE Test Set	Multimeter Minus at J2352			
OSCILLATOR AND MULTIPLIERS AND 1ST MIXER					
1	D (MULT-1 on DFE)	Pin 4	T8 (on 1st OSC/MULT) (L5 on ICOM version)	Maximum	Tune T8 or L5 for maximum meter reading.
2	D (MULT-1 on DFE)	Pin 4	L1 (on MULT Bd)	Minimum	Tune L1 for minimum meter reading.
3	G (MULT-2 on DFE)	Pin 1	T8 or L5 (on 1st OSC/ MULT) L1 and L2 (on MULT Bd)	Maximum	Tune T8 or L5, L1 and L2 for maximum meter reading. If two peaks occur, use the peak that occurs with the slug nearest the top of the coil form.
4	G (MULT-2 on DFE)	Pin 1	C2364	Minimum	Tune C2364 for a small dip in in meter reading.
5	A (DISC on Receiver)	Pin 10		Zero	Connect Test Set plug to receiver metering jack J442. Insert signal generator probe into H2311 and adjust signal generator for discriminator zero.
6	B (2nd IF Amp on Receiver)	Pin 2	T4, C2364 and C2365	Maximum	Tune T4, C2364 and C2365 for maximum meter reading.
7	B (2nd IF Amp on Receiver)	Pin 2	L3 (on 1st Mixer)	Maximum	Apply an on-frequency signal as above. Tune L3 for maximum meter reading, keeping signal below saturation. If two peaks occur, use the peak that occurs with the slug nearest the bottom of the coil form.

RF CIRCUITS

8	B (2nd IF Amp on Receiver)	Pin 2	A2353-L3, C2359, C2358, C2357, & C2356	Maximum	Apply an on-frequency signal into holes as shown below. Insert probe into hole only deep enough to obtain a reading.  Insert Probe In: Tune: 1. H2311 A2353-L3, C2359 and C2358 2. H2310 C2356, C2357 and C2358
9	B (2nd IF Amp on Receiver)	Pin 2	C2355, C2356, C2357, C2358, C2359 and A2353-L3	See Procedure	For standard models, apply an on-frequency signal to the antenna jack (J1) and tune C2355 for maximum meter reading. Then retune C2356 thru C2359 and A2353-L3 for best sensitivity.
10	B (2nd IF Amp on Receiver)	Pin 2	C2351, C2352, C2355 thru C2359 and A2353-L3	See Procedure	For models with UHS, apply an on-frequency signal to the antenna jack (J1) and tune C2351 and C2352 for maximum meter reading. Then retune C2351, C2352, C2355 thru C2359 and A2353-L3 for best sensitivity.

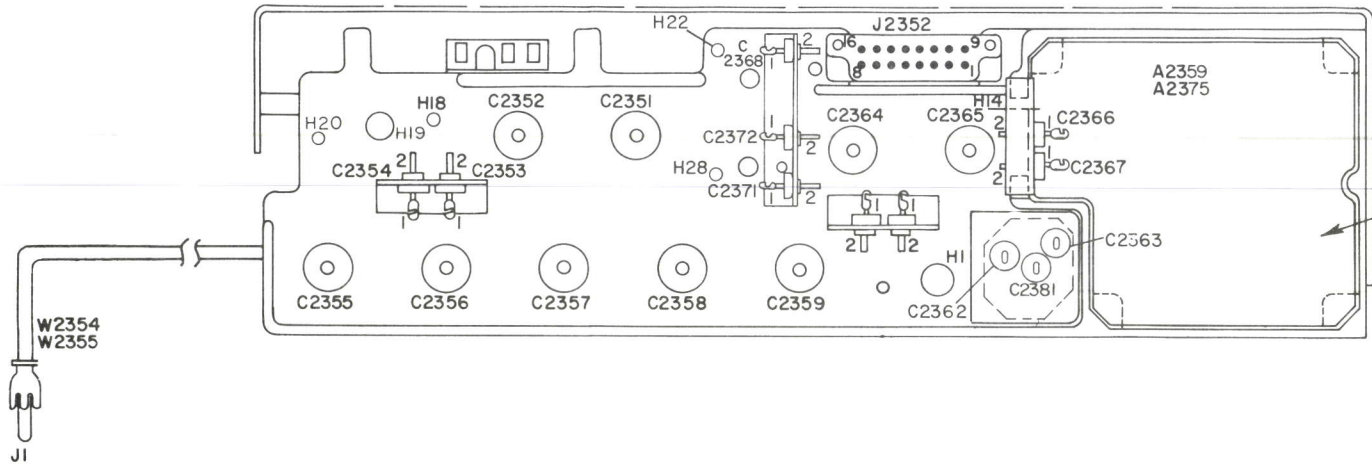
FREQUENCY ADJUSTMENT

11	A (DISC 2nd IF Amp on Receiver)	Pin 10	C9 on 1st OSC/MULT (C10, C11 and C12 for multi-frequency)	Zero	Apply a 10 $\mu$ V or greater on-frequency signal to the antenna jack, and adjust C9 for zero discriminator reading. In multi-frequency units, tune C10, C11 or C12 as required.  NOTE  For proper frequency control of the receiver, it is recommended that all frequency adjustments be made when the equipment is at a temperature of approximately 75°F. In no case should frequency adjustments be made when the equipment is outside the temperature range of 50° to 90°F.
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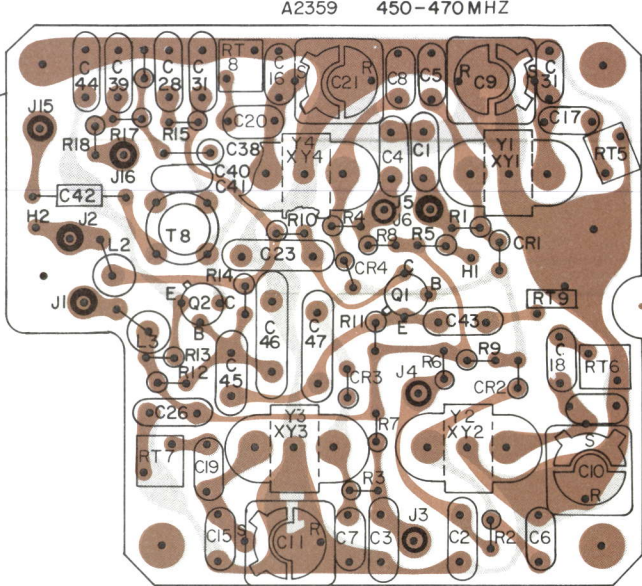
ALIGNMENT PROCEDURE

450-470 MHZ, DUAL FRONT END  
19D413487G1 & G2

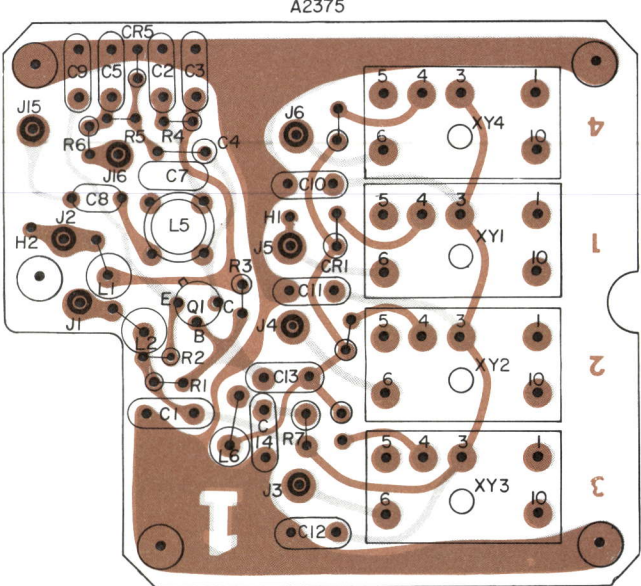
TOP VIEW



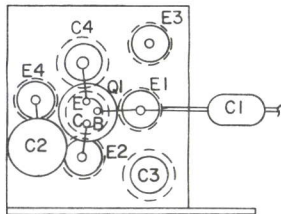
1ST OSCILLATOR/MULTIPLIER



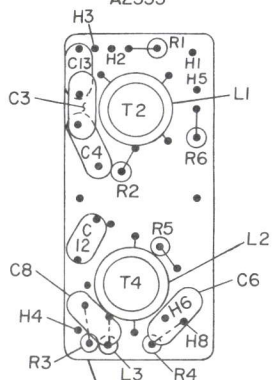
1ST OSCILLATOR/MULTIPLIER (WITH ICOM)



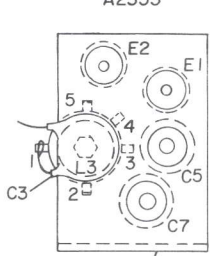
RF AMPLIFIER  
A2352  
(U.H.S. MODEL ONLY)



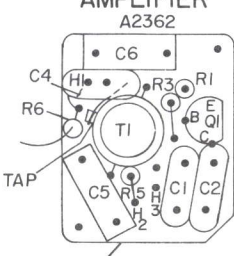
MULTIPLIER  
A2355



1ST MIXER  
A2353



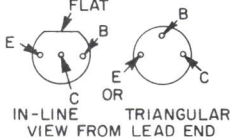
HI IF  
AMPLIFIER  
A2362



FET LEAD IDENTIFICATION  
FOR Q1 OF A2352 & A2353



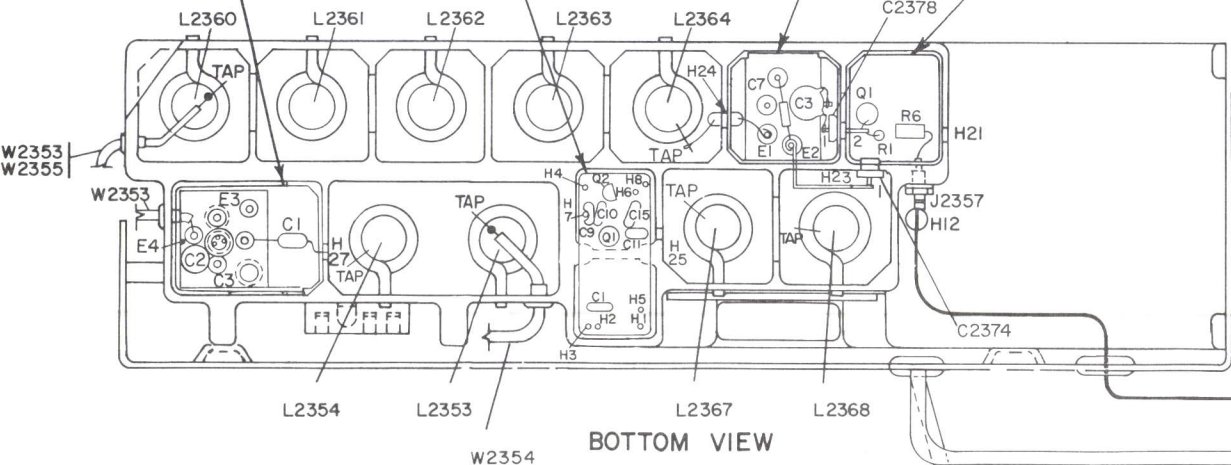
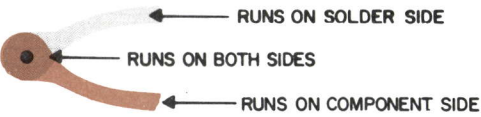
TRANSISTOR  
LEAD IDENTIFICATION



NOTE: LEAD ARRANGEMENT, AND NOT  
CASE SHAPE, IS DETERMINING  
FACTOR FOR LEAD IDENTIFICATION.

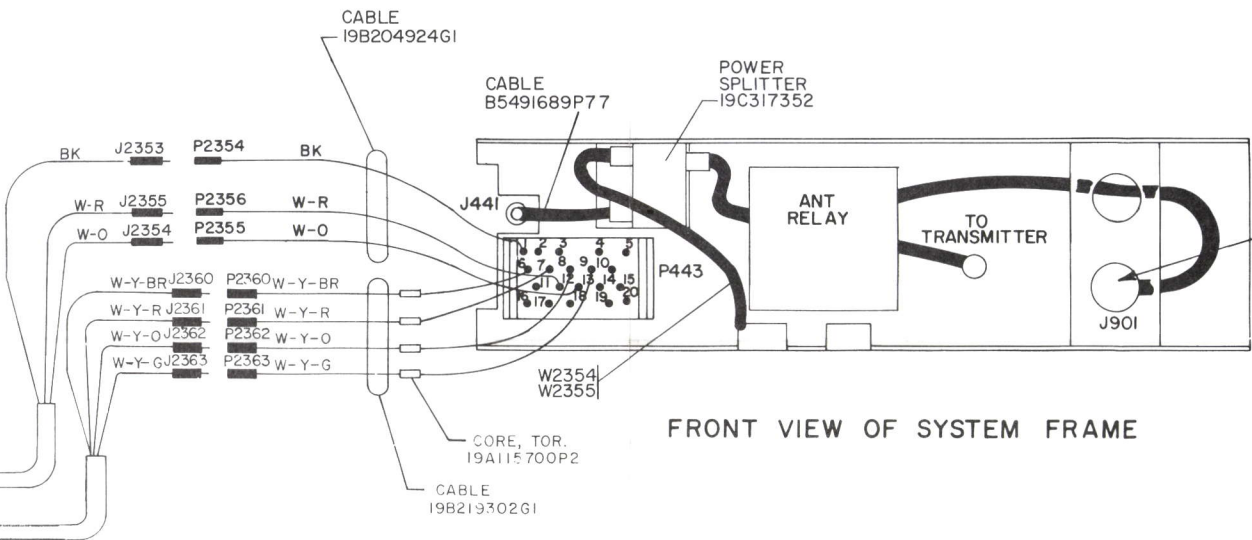
(19B204934, Sh. 1, Rev. 1)  
(19B204934, Sh. 2, Rev. 1)

(19B216041, Sh. 1, Rev. 2)  
(19B216041, Sh. 2, Rev. 2)



BOTTOM VIEW

TO RECEIVER  
CRYSTAL FILTER



FRONT VIEW OF SYSTEM FRAME

OUTLINE DIAGRAM

450—470 MHZ, DUAL FRONT END  
19D413487G1 & G2

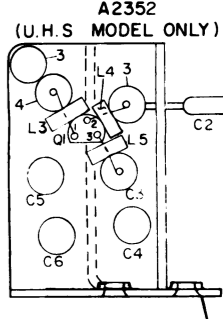
(19R621385, Rev. 5)



SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
A2353		FIRST MIXER ASSEMBLY 19C31974G1															
C1	5496218P312	Ceramic disc: 18 pf ±10%, 500 VDCW, temp coef -150 PPM.	L3	19B209420P1	Coil, RF: 0.10 µh ±5%, 0.08 ohms DC res max; sim to Jeffers 4416.	C39	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C10	5494481P112	Ceramic disc: 1000 pf ±10%, 500 VDCW; sim to RMC Type JF Discap.	C2364 and C2365		(See Miscellaneous).	TB4	7487424P23	Miniature, phen: 1 terminal.
C2		----- CAPACITORS -----	Q1	19A115329P2	----- TRANSISTORS -----	C41	5491798P7	Coil.	C2366 thru C2368	5493392P7	Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.	W2353	19A122550G1	RF: approx 4 inches long.	W2354	19A122563G1	RF: approx 27 inches.
C3	5496218P344	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef -150 PPM.	Q2	19A115991P1	Silicon, NPN.	C42	5491601P130	Molded: 3.3 pf ±5%, 500 VDCW; sim to Quality Components Type MC.	C2369	5496267P11	Tantalum: 68 pf ±20%, 15 VDCW; sim to Sprague Type 150B.	W2355	19A122563G2	RF: approx 21 inches.	W2356		CABLE ASSEMBLY 19B219304G2
C4	19A116080P1	Polyester: 0.01 pf ±20%, 50 VDCW.	R1	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	C43	5496218P53	Ceramic disc: 38 pf ±5%, 500 VDCW, temp coef 0 PPM.	C2370	19A115680P4	Electrolytic: 50 µf +150% -10%, 25 VDCW; sim to Mallory Type TT.			----- JACKS AND RECEPTACLES -----	J2360 thru J2363	7147199P1	Connector: male contact; sim to Winchester Electronics 21803.
C5	5493392P107	Ceramic, stand-off: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type S5SD.	R2	3R152P181J	Composition: 180 ohms ±5%, 1/4 w.	C44	5490008P135	Silver mica: 220 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	C2371 and C2372	5493392P7	Ceramic, feed-thru: .001 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.			----- INDUCTORS -----	L2376 thru L2383	19A115700P2	Toroidal core.
C6	19A116080P1	Polyester: 0.01 pf ±20%, 50 VDCW.	R3	3R152P100K	Composition: 10 ohms ±10%, 1/4 w.	C45	5490008P35	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	C2373	7774750P4	Ceramic disc: .001 pf +100% -0%, 500 VDCW.			----- JACKS AND RECEPTACLES -----	P2364 thru P2367	4029840P2	Contact, electrical: sim to Amp 42827-2.
C7	5493392P7	Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW; sim to Allen Bradley Type FASC.	R4	3R152P471K	Composition: 470 ohms ±10%, 1/4 w.	C46	5496219P563	Ceramic disc: 100 pf ±5%, 500 VDCW, temp coef -330 PPM.	C2378	5493392P3	Ceramic, feed-thru: 47 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.			----- INDUCTORS -----			
C8		----- TERMINALS -----	R5	3R152P680J	Composition: 68 ohms ±5%, 1/4 w.	C47	5496219P767	Ceramic disc: 150 pf ±5%, 500 VDCW, temp coef -750 PPM.	C2380	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.			----- PLUGS -----			
E1 and E2	19B209055P8	Terminal, feed thru: sim to Electrical Industries ABAS-40WSS.	R6	3R152P273K	Composition: 27K ohms ±10%, 1/4 w.			----- DIODES AND RECTIFIERS -----	C2381	5493392P7	Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.			RECEIVER MODIFICATION KIT 19A127735G1			
L1	19A127430G1	Choke.	R7	3R152P100K	Composition: 10 ohms ±10%, 1/4 w.	CR1 thru CR4	19A115603P1	Silicon.	Q1*	19A115440P1	Silicon, NPN.			DIODE ASSEMBLY 19B219305G2			
L2		(Part of L3).	T2		----- TRANSFORMERS -----	CR6	19A115250P1	Silicon.	C1	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	J2352	19B205689G2	Connector: 18 contacts rated at 5 amps min at 1000 VDC max.			
L3	19B216440G1	Coil assembly, includes:			COIL ASSEMBLY 19B216373G2			----- JACKS AND RECEPTACLES -----	C2	7489162P21	Silver mica: 56 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	J2353 and J2354	7147199P1	Connector: male contact; sim to Winchester Electronics 21803.			
C2	5496218P249	Capacitor, ceramic disc: 27 pf ±5%, 500 VDCW, temp coef -80 PPM.	C3	5496218P248	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef -80 PPM.			----- INDUCTORS -----	C3	5496218P650	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -470 PPM.	J2356	7147199P1	Connector: male contact; sim to Winchester Electronics 21803.			
C8	19A116114P12	Ceramic: 3.3 pf ±5%, 100 VDCW; temp coef 0 PPM.	L1	19B216373P5	Coil.			----- TRANSISTORS -----	R1	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	J2357	19A115465P1	Connector, coaxial: sim to Micon Electronics Type 1104.	C1	5493392P107	Ceramic, stand off: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type S5SD.
L2	19B209420P113	Coil, RF: 1 µh ±10%, 0.74 ohms DC res max; sim to Jeffers 4428-6K.	T4		COIL ASSEMBLY 19B216374G2			----- INDUCTORS -----	R2	3R152P151J	Composition: 150 ohms ±5%, 1/4 w.			(Part of W2356).			
	5491798P8	Tuning slug.			----- CAPACITORS -----			----- TRANSISTORS -----	R3	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.			----- INDUCTORS -----	CR1 thru CR3	19A115250P1	Silicon.
Q1*	19A116960P1	N Type, field effect; sim to Type 2N4416.	C6	5496218P237	Ceramic disc: 6.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.			----- TRANSISTORS -----	R4	3R152P101K	Composition: 100 ohms ±15, 1/4 w.	L2353	19B204938G8	Coil.			
		In Cl of REV E & earlier: In G of REV D & earlier:	C8	5496218P246	Ceramic disc: 20 pf ±5%, 500 VDCW, temp coef -80 PPM.	Q1 and Q2	19A115330P1	Silicon, NPN.	R5 and R6	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w.	L2354	19B204938G16	Coil.			
	19A116154P1	N Channel, field effect.			----- INDUCTORS -----			----- RESISTORS -----	R1 thru R4	3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.	L2360	19B204938G12	Coil.			
R1	3R152P302J	Composition: 3K ohms ±5%, 1/4 w.	L2	19B216374P7	Coil.			----- TRANSISTORS -----	R5 thru R8	3R152P104K	Composition: 0.10 megohm ±10%, 1/4 w.	L2361 thru L2363	19B204938P14	Coil.			
R2 and R3	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.		5491798P7	Tuning slug.			----- RESISTORS -----	R9	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.	L2364	19B204938G18	Coil.			
A2355		COMPONENT BOARD 19B216360G2	A2359		FIRST OSCILLATOR/MULTIPLIER 19B204419G24			----- TRANSISTORS -----	R10	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	L2365 and L2366	19A115700P2	Toroidal core.			
C1	19A116655P12	Ceramic disc: 330 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C1	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.			----- INDUCTORS -----	R11 and R12	3R152P102J	Composition: 3K ohms ±5%, 1/4 w.	L2367	19B204938G20	Coil.			
C3		----- CAPACITORS -----	C5	5496219P751	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -750 PPM.			----- TRANSISTORS -----	R13	3R152P151J	Composition: 150 ohms ±5%, 1/4 w.	L2368	19B204938G16	Coil.			
C4	5496203P149	Ceramic disc: 220 pf ±10%, 500 VDCW, temp coef -3300 PPM.	C8	5491271P106	Variable, subminiature: approx 2.1-12.7 pf, ±50 v peak; sim to SF Johnson 189.			----- TRANSFORMERS -----	R14	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	L2369 and L2370	7488079P18	Choke, RF: 15 µh ±10%, 1.2 ohms DC res: sim to Jeffers 4411-8K.			
C6		(Part of T2).	C9		----- THERMISTORS -----			----- TRANSISTORS -----	R15	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	L2371 and L2372	7488079P6	Choke, RF: 1.0 µh ±10%, 0.30 ohms DC res: sim to Jeffers 4411-8K.			
C8		(Part of T4).	C12	5496219P40	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.			----- TRANSISTORS -----	R17 and R18	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w.	L2373	19A127433P1	Coil.			
C10	5496203P149	Ceramic disc: 220 pf ±10%, 500 VDCW, temp coef -3300 PPM.	C19	19C300685P93	Ceramic disc: 5 pf ±0.1 pf, 500 VDCW, temp coef 0 PPM.			----- TRANSISTORS -----	RT5 thru RT8	19B209284P7	Disc: 62 ohms res nominal at 25°C, color code violet.	L2376 thru L2383		(Part of W2356).			
C11	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.	C23	5494481P114	Ceramic disc: 2000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.			----- TRANSISTORS -----	RT9	19B209284P8	Disc: 945 ohms res nominal at 25°C, color code gray.	P2351 and P2355	4029840P2	Contact, electrical: sim to Amp 42827-2.			
C12	5494481P107	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C26	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.			----- TRANSISTORS -----			----- CAPACITORS -----	P2364 thru P2367	19A129072P2	Plate. (Used with Diode Assembly).			
C13	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C28	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.			----- TRANSFORMERS -----			----- CAPACITORS -----			MISCELLANEOUS			
C15	5494481P7	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C31	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.			----- CAPACITORS -----	C7	5496219P238	Ceramic disc: 7 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.	C2353 and C2354	5493392P7	Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.			
		----- INDUCTORS -----	C38	5491601P123	Molded: 1.5 pf ±5%, 500 VDCW; sim to Quality Components Type MC.			----- CAPACITORS -----	C8			C2355 thru C2359		(See Miscellaneous).			
L1		(Part of T2).						----- TRANSISTORS -----	C9	5490008P135	Silver mica: 220 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	C2360 thru C2363	5493392P7	Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.			
L2		(Part of T4).						----- TRANSISTORS -----									

Outline Diagram Was:

RF AMPLIFIER  
A2352  
(U H S MODEL ONLY)



PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A & B - Model 19D413487G1, G2

Incorporated into initial shipment.

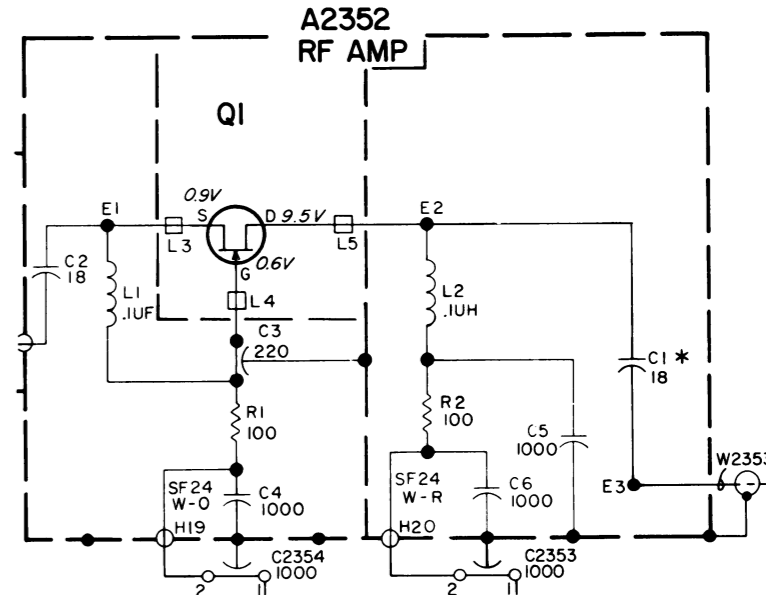
REV. C - Model 19D413487G1, G2

To improve receiver intermodulation performance. Changed Q1 and R3 on IF Amplifier assembly 19B216356G1.

REV. D - Model 19D413487G1

To incorporate improved design. Replaced existing RF Amplifier Assembly A2352 (19C317950G1) with a new RF Amplifier Assembly (19C320687G1).

Schematic Diagram 19B621327 & 19B621328 Was:



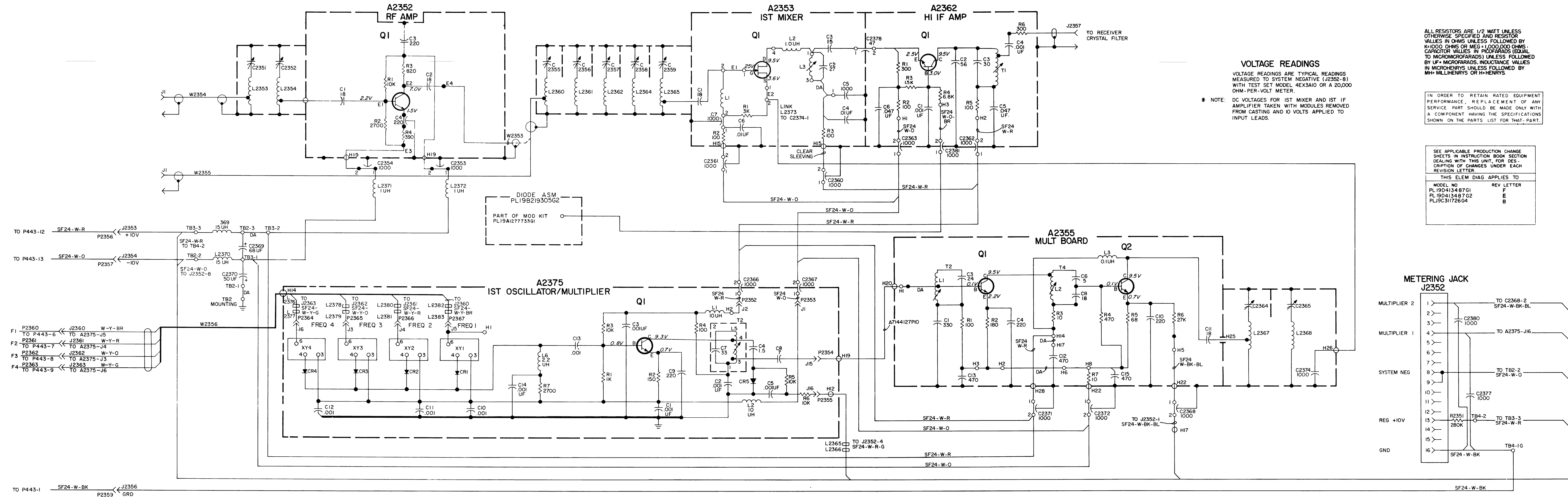
\* In some units C1 may be 27 pf

REV. E - Model 19D413487G1

To improve receiver sensitivity. Changed A2353-C1 & A2353-C3

REV. F - Model 19D413487G1

To incorporate new transistor. Changed Q1.



(19R621328, Rev. 12)